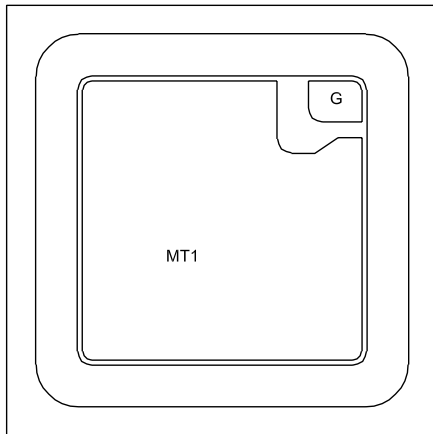


PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	90 x 90 MILS
Die Thickness	8.6 MILS ± 0.6 MILS
MT1 Bonding Pad Area	61 x 48 MILS
Gate Bonding Pad Area	11 x 9.8 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



R0

BACKSIDE MT2

GROSS DIE PER 4 INCH WAFER

1,310

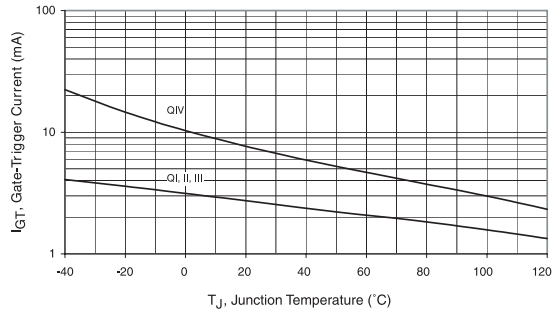
PRINCIPAL DEVICE TYPES

2N6075A
CQ202-4MS
CQ223-4M
CQD-4M

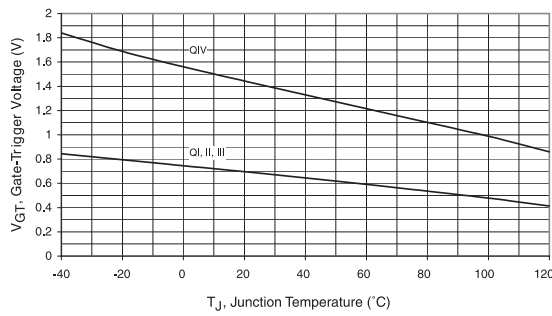
145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R1 (19 -May 2005)

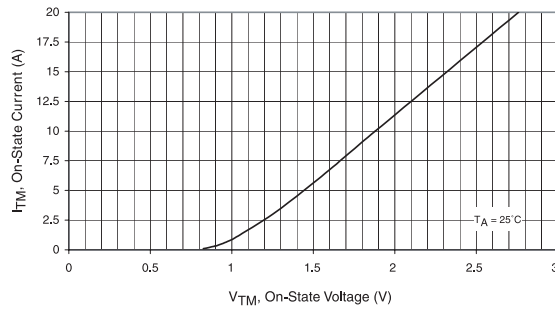
Typical Gate-Trigger Current



Typical Gate-Trigger Voltage



Typical On-State Voltage



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